

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A pattern formation method comprising the steps of:
forming a resist film of a chemically amplified resist material;
performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying, onto said resist film, a an immersion solution including a basic compound; and
forming a resist pattern by developing said resist film after the pattern exposure.
2. (Original) The pattern formation method of Claim 1,
wherein said solution is water or perfluoropolyether.
3. (Currently amended) The pattern formation method of Claim 1,
wherein said exposing light is KrF excimer laser, ArF excimer laser, ~~or~~ F₂ laser, KrAr
laser or Ar₂ laser.
4. (Currently amended) A pattern formation method comprising the steps of:
forming a resist film of a chemically amplified resist material;
performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying, onto said resist film, a an immersion solution including a basic polymer; and
forming a resist pattern by developing said resist film after the pattern exposure.
5. (Original) The pattern formation method of Claim 4,
wherein said solution is water or perfluoropolyether.

6. (Currently amended) The pattern formation method of Claim 4,
wherein said exposing light is KrF excimer laser, ArF excimer laser, ~~or~~ F₂ laser, KrAr
laser or Ar₂ laser.
7. (Currently amended) The pattern formation method comprising the steps of:
forming a resist film of a chemically amplified resist material;
performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying, onto said resist film, a an immersion solution including a compound for
generating a base through irradiation with light; and
forming a resist pattern by developing said resist film after the pattern exposure.
8. (Original) The pattern formation method of Claim 7,
wherein said solution is water or perfluoropolyether.
9. (Currently amended) The pattern formation method of Claim 7,
wherein said exposing light is KrF excimer laser, ArF excimer laser, ~~or~~ F₂ laser, KrAr
laser or Ar₂ laser.
10. (Currently amended) A pattern formation method comprising the steps of:
forming a resist film of a chemically amplified resist material;
performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying, onto said resist film, a an immersion solution including a compound for
generating a base through application of heat; and

forming a resist pattern by developing said resist film after the pattern exposure.

11. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a primary aliphatic amine, a secondary aliphatic amine, a tertiary aliphatic amine, an aromatic amine, an amide derivative, an imide derivative, or a compound having a hydroxyl group and including nitrogen.

12. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a primary aliphatic amine such as ammonia, methylamine, ethylamine, n-propylamine, isopropylamine, n-butylamine or isobutylamine.

13. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a secondary aliphatic amine such as dimethylamine, diethylamine, di-n-propylamine, diisopropylamine, di-n-butylamine, diisobutylamine, di-sec-butylamine, dipentylamine, dicyclopentylamine, dihexylamine or dicyclohexylamine.

14. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a tertiary aliphatic amine such as trimethylamine, triethylamine, tri-n-propylamine, triisopropylamine, tri-n-butylamine, triisobutylamine, tri-sec-butylamine, tripentylamine, tricyclopentylamine, trihexylamine, tricyclohexylamine, dimethylethylamine, methylethylpropylamine, benzylamine, phenethylamine or benzyldimethylamine.

15. (Original) The pattern formation method of Claim 1, wherein said basic compound is an aromatic amine such as diphenyl(p-tolyl)amine, methyldiphenylamine, triphenylamine, phenylenediamine, naphthylamine, diaminonaphthalene, an aniline derivative, a pyrrole derivative, an oxazole derivative, a thiazole derivative, an imidazole derivative, a pyrroline derivative, a pyrrolidine derivative, a pyridine derivative or a quinoline derivative.

16. (Original) The pattern formation method of Claim 1, wherein said basic compound is an aniline derivative such as aniline, *N*-methylaniline, *N*-ethylaniline, *N*-propylaniline, *N,N*-dimethylaniline, 2-methylaniline, 3-methylaniline, 4-methylaniline, ethylaniline, propylaniline or trimethylaniline.

17. (Original) The pattern formation method of Claim 1, wherein said basic compound is a pyrrole derivative such as pyrrole, 2H-pyrrole, 1-methylpyrrole, 2,4-dimethylpyrrole or *N*-methylpyrrole.

18. (Original) The pattern formation method of Claim 1, wherein said basic compound is an oxazole derivative such as oxazole or isoxazole.

19. (Original) The pattern formation method of Claim 1, wherein said basic compound is a thiazole derivative such as thiazole or isothiazole.

20. (Original) The pattern formation method of Claim 1,

wherein said basic compound is an imidazole derivative such as imidazole or 4-methylimidazole.

21. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a pyrroline derivative such as pyrroline or 2-methyl-1-pyrroline.

22. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a pyrrolidine derivative such as pyrrolidine, *N*-methylpyrrolidine or *N*-methylpyrrolidone.

23. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a pyridine derivative such as pyridine, methylpyridine, ethylpyridine, propylpyridine, butylpyridine, 4-(1-butylpentyl)pyridine, dimethylpyridine, trimethylpyridine, triethylpyridine, phenylpyridine, aminopyridine or dimethylaminopyridine.

24. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a quinoline derivative such as quinoline or 3-quinolinecarbonitrile.

25. (Original) The pattern formation method of Claim 1,

wherein said basic compound is an amide derivative such as formamide, *N*-methylformamide, *N,N*-dimethylformamide, acetamide, *N*-methylacetamide, *N,N*-dimethylacetamide or benzamide.

26. (Original) The pattern formation method of Claim 1,
wherein said basic compound is an imide derivative such as phthalimide, succinimide or maleimide.

27. (Original) The pattern formation method of Claim 1,
wherein said basic compound is a compound having a hydroxyl group and including nitrogen such as 2-hydroxypyridine, monoethanolamine, diethanolamine, triethanolamine, *N*-ethyldiethanolamine, *N,N*-diethylethanolamine, triisopropanolamine, 2,2'-iminodiethanol, 2-aminoethanol, 3-amino-1-propanol, 4-amino-1-butanol, 2-(2-hydroxyethyl)pyridine, 1-(2-hydroxyethyl)piperazine, piperidineethanol, 1-(2-hydroxyethyl)pyrrolidine, 1-(2-hydroxyethyl)-2-pyrrolidinone, 3-piperizino-1,2-propanediol, 3-tropanol, 1-methyl-2-pyrrolidineethanol, 1-aziridineethanol or *N*-(2-hydroxyethyl)phthalimide.

28. (Original) The pattern formation method of Claim 4,
wherein said basic polymer is poly-*N,N*-dimethylaminomethylstyrene, polyaniline, polyethylenimine, polyvinylamine, polyallylamine, polyornithine or polylysine.

29. (Original) The pattern formation method of Claim 7,

wherein said compound for generating a base through irradiation with light is an O-acyl oxime.

30. (Original) The pattern formation method of Claim 7,
wherein said compound for generating a base through irradiation with light is an O-acyl oxime such as O-acryloylacetophenone oxime or O-acryloylacetophenone oxime.

31. (Original) The pattern formation method of Claim 10,
wherein said compound for generating a base through application of heat is an acylsulfonyl.

32. (Original) The pattern formation method of Claim 10,
wherein said compound for generating a base through application of heat is p-phenacylsulfonylstyrene.

33. (Original) The pattern formation method of Claim 10,
wherein said solution is water or perfluoropolyether.

34. (Currently amended) The pattern formation method of Claim 10,
wherein said exposing light is KrF excimer laser, ArF excimer laser, ~~or~~ F₂ laser, KrAr laser or Ar₂ laser.